

CMSSH-3
CMSSH-3A
CMSSH-3C
CMSSH-3S
SURFACE MOUNT
SUPERmini™
SILICON SCHOTTKY DIODES

SUPERmini™



SOT-323 CASE

Central™
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMSSH-3 Series types are Silicon Schottky Diodes, epoxy molded in a SUPERmini™ surface mount package, designed for fast switching applications requiring a low forward voltage drop.

CMSSH-3: SINGLE
 CMSSH-3A: DUAL, COMMON ANODE
 CMSSH-3C: DUAL, COMMON CATHODE
 CMSSH-3S: DUAL, IN SERIES

MARKING CODE: 95D
MARKING CODE: B1D
MARKING CODE: B2D
MARKING CODE: A5D

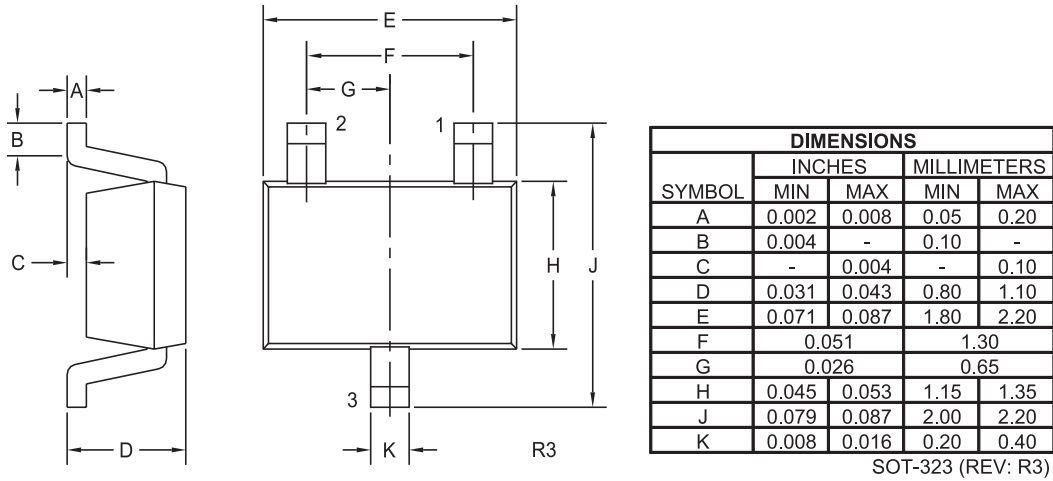
MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

	SYMBOL		UNITS
Peak Repetitive Reverse Voltage	V_{RRM}	30	V
Continuous Forward Current	I_F	100	mA
Peak Repetitive Forward Current	I_{FRM}	200	mA
Forward Surge Current, $t_p=10\text{ms}$	I_{FSM}	750	mA
Power Dissipation	P_D	275	mW
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
Thermal Resistance	Θ_{JA}	455	$^\circ\text{C/W}$

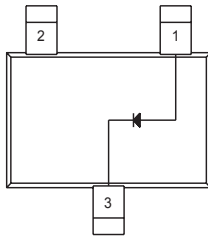
ELECTRICAL CHARACTERISTICS PER DIODE: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
BV_R	$I_R=100\mu\text{A}$	30			V
V_F	$I_F=2.0\text{mA}$		0.29	0.33	V
V_F	$I_F=15\text{mA}$		0.40	0.45	V
V_F	$I_F=100\text{mA}$		0.74	1.00	V
I_R	$V_R=25\text{V}$		90	500	nA
I_R	$V_R=25\text{V}, T_A=100^\circ\text{C}$		25	100	μA
C_T	$V_R=1.0\text{V}, f=1\text{ MHz}$		7.0		pF
t_{rr}	$I_F=I_R=10\text{mA}, I_{rr}=1.0\text{mA}, R_L=100\Omega$			5.0	ns

SOT-323 CASE - MECHANICAL OUTLINE

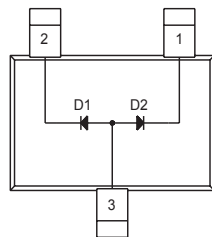


PIN CONFIGURATION



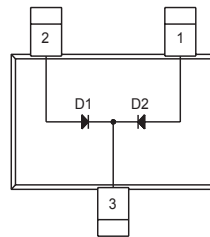
CMSSH-3
 1) Anode
 2) No Connection
 3) Cathode

MARKING CODE:
 95D



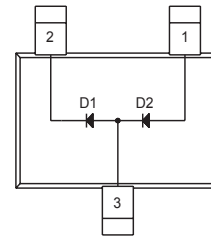
CMSSH-3A
 1) Cathode D2
 2) Cathode D1
 3) Anode D1, D2

MARKING CODE:
 B1D



CMSSH-3C
 1) Anode D2
 2) Anode D1
 3) Cathode D1, D2

MARKING CODE:
 B2D



CMSSH-3S
 1) Anode D2
 2) Cathode D1
 3) Anode D1, Cathode D2

MARKING CODE:
 A5D